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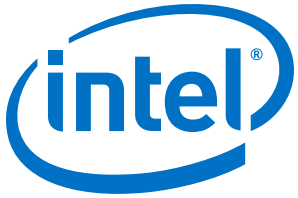

Intel® MAX® 10 FPGA Device Datasheet

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Contents

Intel® MAX® 10 FPGA Device Datasheet

This datasheet describes the electrical characteristics, switching characteristics, configuration specifications, and timing for Intel MAX® 10 devices.

Table 1. Intel MAX 10 Device Grades and Speed Grades Supported

Device Grade	Speed Grade Supported
Commercial	• –C7 • –C8 (slowest)
Industrial	• –I6 (fastest) • –I7
Automotive	• –A6 • –A7

Note: The –I6 and –A6 speed grades of the Intel MAX 10 FPGA devices are not available by default in the Intel Quartus® Prime software. Contact your local Intel sales representatives for support.

Related Information

Device Ordering Information, Intel MAX 10 FPGA Device Overview
Provides more information about the densities and packages of devices in the Intel MAX 10.

Electrical Characteristics

The following sections describe the operating conditions and power consumption of Intel MAX 10 devices.

Operating Conditions

Intel MAX 10 devices are rated according to a set of defined parameters. To maintain the highest possible performance and reliability of the Intel MAX 10 devices, you must consider the operating requirements described in this section.

Absolute Maximum Ratings

This section defines the maximum operating conditions for Intel MAX 10 devices. The values are based on experiments conducted with the devices and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied for these conditions.

Caution: Conditions outside the range listed in the absolute maximum ratings tables may cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse effects on the device.

Single Supply Devices Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings for Intel MAX 10 Single Supply Devices

Symbol	Parameter	Min	Max	Unit
V_{CC_ONE}	Supply voltage for core and periphery through on-die voltage regulator	–0.5	3.9	V
V_{CCIO}	Supply voltage for input and output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage for phase-locked loop (PLL) regulator and analog-to-digital converter (ADC) block (analog)	–0.5	3.9	V

Dual Supply Devices Absolute Maximum Ratings

Table 3. Absolute Maximum Ratings for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage for core and periphery	–0.5	1.63	V
V_{CCIO}	Supply voltage for input and output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage for PLL regulator (analog)	–0.5	3.41	V

continued...

Symbol	Parameter	Min	Max	Unit
V_{CCD_PLL}	Supply voltage for PLL regulator (digital)	–0.5	1.63	V
V_{CCA_ADC}	Supply voltage for ADC analog block	–0.5	3.41	V
V_{CCINT}	Supply voltage for ADC digital block	–0.5	1.63	V

Absolute Maximum Ratings

Table 4. Absolute Maximum Ratings for Intel MAX 10 Devices

Symbol	Parameter	Min	Max	Unit
V_I	DC input voltage	–0.5	4.12	V
I_{OUT}	DC output current per pin	–25	25	mA
T_{STG}	Storage temperature	–65	150	°C
T_J	Operating junction temperature	–40	125	°C

Maximum Allowed Overshoot During Transitions over a 11.4-Year Time Frame

During transitions, input signals may overshoot to the voltage listed in the following table and undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.

The maximum allowed overshoot duration is specified as a percentage of high time over the lifetime of the device. A DC signal is equivalent to 100% duty cycle.

For example, a signal that overshoots to 4.17 V can only be at 4.17 V for ~11.7% over the lifetime of the device; for a device lifetime of 11.4 years, this amounts to 1.33 years.

Table 5. Maximum Allowed Overshoot During Transitions over a 11.4-Year Time Frame for Intel MAX 10 Devices

Condition (V)	Overshoot Duration as % of High Time	Unit
4.12	100.0	%
4.17	11.7	%
4.22	7.1	%
4.27	4.3	%

continued...

Condition (V)	Overshoot Duration as % of High Time	Unit
4.32	2.6	%
4.37	1.6	%
4.42	1.0	%
4.47	0.6	%
4.52	0.3	%
4.57	0.2	%

Recommended Operating Conditions

This section lists the functional operation limits for the AC and DC parameters for Intel MAX 10 devices. The tables list the steady-state voltage values expected from Intel MAX 10 devices. Power supply ramps must all be strictly monotonic, without plateaus.

Single Supply Devices Power Supplies Recommended Operating Conditions

Table 6. Power Supplies Recommended Operating Conditions for Intel MAX 10 Single Supply Devices

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{CC_ONE}(1)	Supply voltage for core and periphery through on-die voltage regulator	—	2.85/3.135	3.0/3.3	3.15/3.465	V
V_{CCIO}(2)	Supply voltage for input and output buffers	3.3 V	3.135	3.3	3.465	V
		3.0 V	2.85	3	3.15	V
		2.5 V	2.375	2.5	2.625	V
		1.8 V	1.71	1.8	1.89	V
		1.5 V	1.425	1.5	1.575	V

continued...

(1) V_{CCA} must be connected to V_{CC_ONE} through a filter.

(2) V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V_{CCA} (1)	Supply voltage for PLL regulator and ADC block (analog)	—	2.85/3.135	3.0/3.3	3.15/3.465	V

Dual Supply Devices Power Supplies Recommended Operating Conditions

Table 7. Power Supplies Recommended Operating Conditions for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{CC}	Supply voltage for core and periphery	—	1.15	1.2	1.25	V
V_{CCIO} (3)	Supply voltage for input and output buffers	3.3 V	3.135	3.3	3.465	V
		3.0 V	2.85	3	3.15	V
		2.5 V	2.375	2.5	2.625	V
		1.8 V	1.71	1.8	1.89	V
		1.5 V	1.425	1.5	1.575	V
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V_{CCA}(4)	Supply voltage for PLL regulator (analog)	—	2.375	2.5	2.625	V
V_{CCD_PLL}(5)	Supply voltage for PLL regulator (digital)	—	1.15	1.2	1.25	V
V_{CCA_ADC}	Supply voltage for ADC analog block	—	2.375	2.5	2.625	V
V_{CCINT}	Supply voltage for ADC digital block	—	1.15	1.2	1.25	V

(3) V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities.

(4) All V_{CCA} pins must be powered to 2.5 V (even when PLLs are not used), and must be powered up and powered down at the same time.

(5) V_{CCD_PLL} must always be connected to V_{CC} through a decoupling capacitor and ferrite bead.

Recommended Operating Conditions

Table 8. Recommended Operating Conditions for Intel MAX 10 Devices

Symbol	Parameter	Condition	Min	Max	Unit
V_I	DC input voltage	—	–0.5	3.6	V
V_O	Output voltage for I/O pins	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial	0	85	°C
		Industrial	–40(6)	100	°C
		Automotive	–40(6)	125	°C
t_{RAMP}	Power supply ramp time	—	(7)	10	ms
I_{Diode}	Magnitude of DC current across PCI* clamp diode when enabled	—	—	10	mA

Programming/Erasure Specifications

Table 9. Programming/Erasure Specifications for Intel MAX 10 Devices

This table shows the programming cycles and data retention duration of the user flash memory (UFM) and configuration flash memory (CFM) blocks.

For more information about data retention duration with 10,000 programming cycles for automotive temperature devices, contact your Intel quality representative.

Erase and reprogram cycles (E/P) (8) (Cycles/page)	Temperature (°C)	Data retention duration (Years)
10,000	85	20
10,000	100	10

(6) –40°C is only applicable to Start of Test, when the device is powered-on. The device does not stay at the minimum junction temperature for a long time.

(7) There is no absolute minimum value for the ramp time requirement. Intel characterized the minimum ramp time at 200 µs.

(8) The number of E/P cycles applies to the smallest possible flash block that can be erased or programmed in each Intel MAX 10 device. Each Intel MAX 10 device has multiple flash pages per device.

DC Characteristics

Supply Current and Power Consumption

Intel offers two ways to estimate power for your design—the Excel-based Early Power Estimator (EPE) and the Intel Quartus Prime Power Analyzer feature.

Use the Excel-based EPE before you start your design to estimate the supply current for your design. The EPE provides a magnitude estimate of the device power because these currents vary greatly with the usage of the resources.

The Intel Quartus Prime Power Analyzer provides better quality estimates based on the specifics of the design after you complete place-and-route. The Power Analyzer can apply a combination of user-entered, simulation-derived, and estimated signal activities that, when combined with detailed circuit models, yield very accurate power estimates.

Related Information

- Early Power Estimator User Guide
  Provides more information about power estimation tools.
- Power Analysis chapter, Intel Quartus Prime Handbook
  Provides more information about power estimation tools.

I/O Pin Leakage Current

The values in the table are specified for normal device operation. The values vary during device power-up. This applies for all V_{CCIO} settings (3.3, 3.0, 2.5, 1.8, 1.5, 1.35, and 1.2 V).

10 µA I/O leakage current limit is applicable when the internal clamping diode is off. A higher current can be the observed when the diode is on.

Input channel leakage of ADC I/O pins due to hot socket is up to maximum of 1.8 mA. The input channel leakage occurs when the ADC IP core is enabled or disabled. This is applicable to all Intel MAX 10 devices with ADC IP core, which are 10M04, 10M08, 10M16, 10M25, 10M40, and 10M50 devices. The ADC I/O pins are in Bank 1A.

Table 10. I/O Pin Leakage Current for Intel MAX 10 Devices

Symbol	Parameter	Condition	Min	Max	Unit
I_I	Input pin leakage current	V_I = 0 V to $V_{CCIOMAX}$	–10	10	µA
I_{OZ}	Tristated I/O pin leakage current	V_O = 0 V to $V_{CCIOMAX}$	–10	10	µA

Table 11. ADC_VREF Pin Leakage Current for Intel MAX 10 Devices

Symbol	Parameter	Condition	Min	Max	Unit
I_{adc_vref}	ADC_VREF pin leakage current	Single supply mode	—	10	µA
		Dual supply mode	—	20	µA

Bus Hold Parameters

Bus hold retains the last valid logic state after the source driving it either enters the high impedance state or is removed. Each I/O pin has an option to enable bus hold in user mode. Bus hold is always disabled in configuration mode.

Table 12. Bus Hold Parameters for Intel MAX 10 Devices

Parameter	Condition	V_{CCIO} (V)												Unit
		1.2		1.5		1.8		2.5		3.0		3.3		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus-hold low, sustaining current	$V_{IN} > V_{IL}$ (maximum)	8	—	12	—	30	—	50	—	70	—	70	—	µA
Bus-hold high, sustaining current	$V_{IN} < V_{IH}$ (minimum)	–8	—	–12	—	–30	—	–50	—	–70	—	–70	—	µA
Bus-hold low, overdrive current	$0 V < V_{IN} < V_{CCIO}$	—	125	—	175	—	200	—	300	—	500	—	500	µA
Bus-hold high, overdrive current	$0 V < V_{IN} < V_{CCIO}$	—	–125	—	–175	—	–200	—	–300	—	–500	—	–500	µA
Bus-hold trip point	—	0.3	0.9	0.375	1.125	0.68	1.07	0.7	1.7	0.8	2	0.8	2	V

Series OCT without Calibration Specifications

Table 13. Series OCT without Calibration Specifications for Intel MAX 10 Devices

This table shows the variation of on-chip termination (OCT) without calibration across process, voltage, and temperature (PVT).

Description	V_{CCIO} (V)	Resistance Tolerance		Unit
		–C7, –I6, –I7, –A6, –A7	–C8	
Series OCT without calibration	3.00	±35	±30	%
	2.50	±35	±30	%
	1.80	±40	±35	%
	1.50	±40	±40	%
	1.35	±40	±50	%
	1.20	±45	±60	%

Series OCT with Calibration at Device Power-Up Specifications

Table 14. Series OCT with Calibration at Device Power-Up Specifications for Intel MAX 10 Devices

OCT calibration is automatically performed at device power-up for OCT enabled I/Os.

Description	V_{CCIO} (V)	Calibration Accuracy	Unit
Series OCT with calibration at device power-up	3.00	±12	%
	2.50	±12	%
	1.80	±12	%
	1.50	±12	%
	1.35	±12	%
	1.20	±12	%

OCT Variation after Calibration at Device Power-Up

The OCT resistance may vary with the variation of temperature and voltage after calibration at device power-up.

Use the following table and equation to determine the final OCT resistance considering the variations after calibration at device power-up.

Table 15. OCT Variation after Calibration at Device Power-Up for Intel MAX 10 Devices

This table lists the change percentage of the OCT resistance with voltage and temperature.

Description	Nominal Voltage	dR/dT (%/°C)	dR/dV (%/mV)
OCT variation after calibration at device power-up	3.00	0.25	–0.027
	2.50	0.245	–0.04
	1.80	0.242	–0.079
	1.50	0.235	–0.125
	1.35	0.229	–0.16
	1.20	0.197	–0.208

Figure 1. Equation for OCT Resistance after Calibration at Device Power-Up

$$\Delta R_V = (V_2 - V_1) \times 1000 \times dR/dV$$

$$\Delta R_T = (T_2 - T_1) \times dR/dT$$

$$\text{For } \Delta R_X < 0; MF_X = 1/(|\Delta R_X|/100 + 1)$$

$$\text{For } \Delta R_X > 0; MF_X = \Delta R_X/100 + 1$$

$$MF = MF_V \times MF_T$$

$$R_{final} = R_{initial} \times MF$$

The definitions for equation are as follows:

- T_1 is the initial temperature.
- T_2 is the final temperature.
- MF is multiplication factor.
- $R_{initial}$ is initial resistance.
- R_{final} is final resistance.

- Subscript x refers to both V and T.
- ΔR_V is variation of resistance with voltage.
- ΔR_T is variation of resistance with temperature.
- dR/dT is the change percentage of resistance with temperature after calibration at device power-up.
- dR/dV is the change percentage of resistance with voltage after calibration at device power-up.
- V_1 is the initial voltage.
- V_2 is final voltage.

The following figure shows the example to calculate the change of 50 Ω I/O impedance from 25°C at 3.0 V to 85°C at 3.15 V.

Figure 2. Example for OCT Resistance Calculation after Calibration at Device Power-Up

$$\Delta R_V = (3.15 - 3) \times 1000 \times -0.027 = -4.05$$

$$\Delta R_T = (85 - 25) \times 0.25 = 15$$

Because ΔR_V is negative,

$$MF_V = 1/(4.05/100 + 1) = 0.961$$

Because ΔR_T is positive,

$$MF_T = 15/100 + 1 = 1.15$$

$$MF = 0.961 \times 1.15 = 1.105$$

$$R_{final} = 50 \times 1.105 = 55.25\Omega$$

Pin Capacitance

Table 16. Pin Capacitance for Intel MAX 10 Devices

Symbol	Parameter	Maximum	Unit
C_{IOB}	Input capacitance on bottom I/O pins	8	pF
C_{IOLRT}	Input capacitance on left/right/top I/O pins	7	pF
C_{LVDSB}	Input capacitance on bottom I/O pins with dedicated LVDS output (9)	8	pF
C_{ADCL}	Input capacitance on left I/O pins with ADC input (10)	9	pF
$C_{VREFLRT}$	Input capacitance on left/right/top dual purpose V_{REF} pin when used as V_{REF} or user I/O pin (11)	48	pF
C_{VREFB}	Input capacitance on bottom dual purpose V_{REF} pin when used as V_{REF} or user I/O pin	50	pF
C_{CLKB}	Input capacitance on bottom dual purpose clock input pins (12)	7	pF
C_{CLKLRT}	Input capacitance on left/right/top dual purpose clock input pins (12)	6	pF

Internal Weak Pull-Up Resistor

All I/O pins, except configuration, test, and JTAG pins, have an option to enable weak pull-up.

(9) Dedicated LVDS output buffer is only available at bottom I/O banks.

(10) ADC pins are only available at left I/O banks.

(11) When V_{REF} pin is used as regular input or output, F_{max} performance is reduced due to higher pin capacitance. Using the V_{REF} pin capacitance specification from device datasheet, perform SI analysis on your board setup to determine the F_{max} of your system.

(12) 10M40 and 10M50 devices have dual purpose clock input pins at top/bottom I/O banks.

Table 17. Internal Weak Pull-Up Resistor for Intel MAX 10 Devices

Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$R_{\_PU}$	Value of I/O pin (dedicated and dual-purpose) pull-up resistor before and during configuration, as well as user mode if the programmable pull-up resistor option is enabled	V_{CCIO} = 3.3 V ± 5%	7	12	34	kΩ
		V_{CCIO} = 3.0 V ± 5%	8	13	37	kΩ
		V_{CCIO} = 2.5 V ± 5%	10	15	46	kΩ
		V_{CCIO} = 1.8 V ± 5%	16	25	75	kΩ
		V_{CCIO} = 1.5 V ± 5%	20	36	106	kΩ
		V_{CCIO} = 1.2 V ± 5%	33	82	179	kΩ

Hot-Socketing Specifications

Table 18. Hot-Socketing Specifications for Intel MAX 10 Devices

Symbol	Parameter	Maximum
$I_{IOPIN(DC)}$	DC current per I/O pin	300 µA
$I_{IOPIN(AC)}$	AC current per I/O pin	8 mA (13)

Hysteresis Specifications for Schmitt Trigger Input

Intel MAX 10 devices support Schmitt trigger input on all I/O pins. A Schmitt trigger feature introduces hysteresis to the input signal for improved noise immunity, especially for signal with slow edge rate.

(13) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|I_{IOPIN}|$ = C dv/dt, in which C is I/O pin capacitance and dv/dt is the slew rate.

Table 19. Hysteresis Specifications for Schmitt Trigger Input for Intel MAX 10 Devices

Symbol	Parameter	Condition	Minimum	Unit
V_{HYS}	Hysteresis for Schmitt trigger input	V_{CCIO} = 3.3 V	180	mV
		V_{CCIO} = 2.5 V	150	mV
		V_{CCIO} = 1.8 V	120	mV
		V_{CCIO} = 1.5 V	110	mV

Figure 3. LVTTL/LVCMOS Input Standard Voltage Diagram

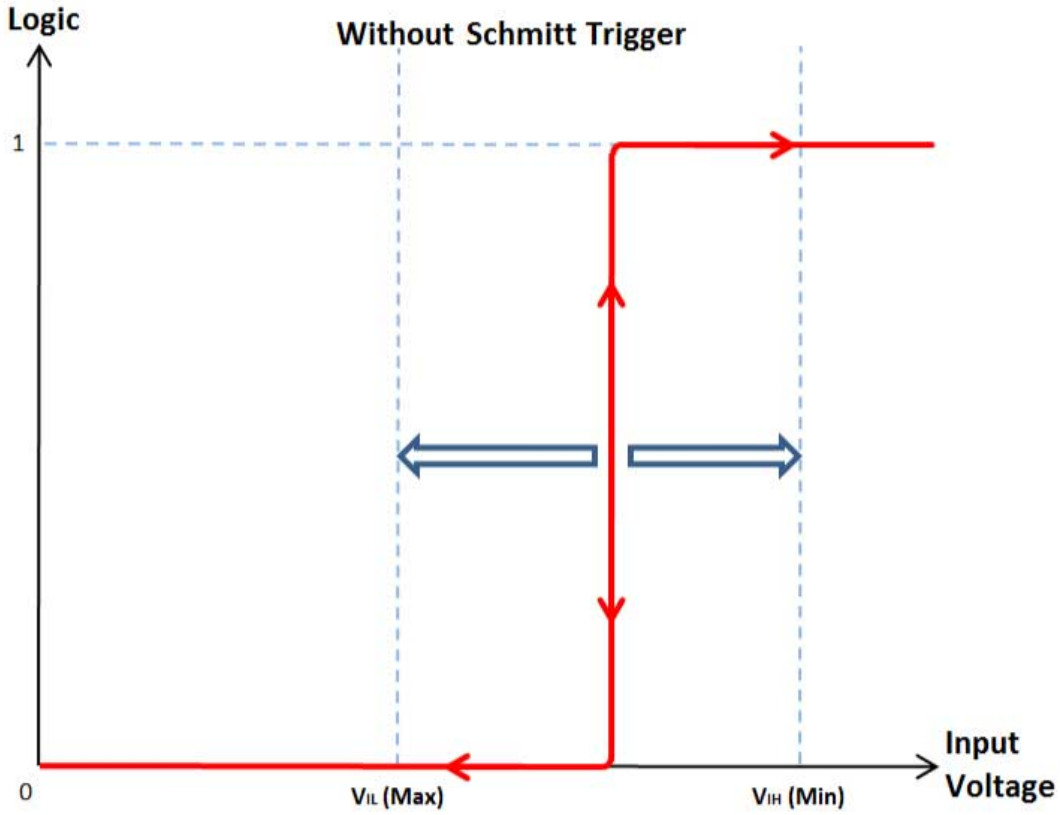
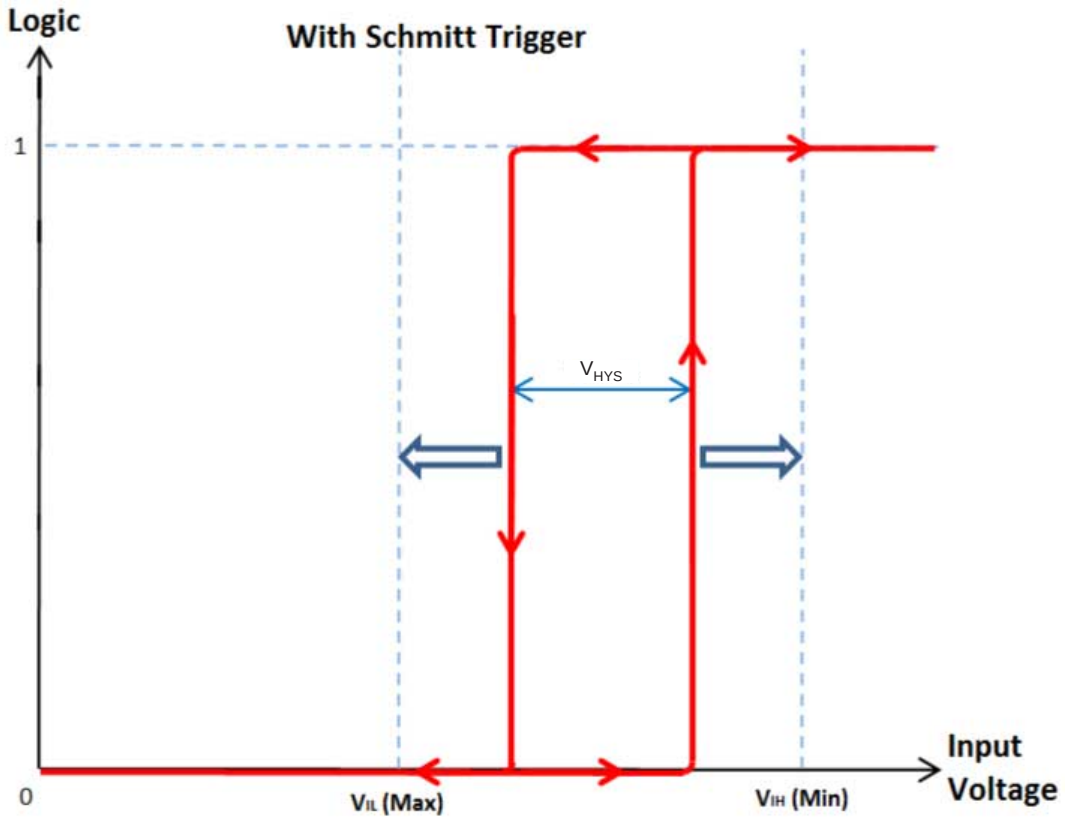


Figure 4. Schmitt Trigger Input Standard Voltage Diagram



I/O Standards Specifications

Tables in this section list input voltage (V_{IH} and V_{IL}), output voltage (V_{OH} and V_{OL}), and current drive characteristics (I_{OH} and I_{OL}) for various I/O standards supported by Intel MAX 10 devices.

For minimum voltage values, use the minimum V_{CCIO} values. For maximum voltage values, use the maximum V_{CCIO} values.

You must perform timing closure analysis to determine the maximum achievable frequency for general purpose I/O standards.

Single-Ended I/O Standards Specifications

Table 20. Single-Ended I/O Standards Specifications for Intel MAX 10 Devices

To meet the I_{OL} and I_{OH} specifications, you must set the current strength settings accordingly. For example, to meet the 3.3-V LVTTL specification (4 mA), you should set the current strength settings to 4 mA. Setting at lower current strength may not meet the I_{OL} and I_{OH} specifications in the datasheet.

I/O Standard	V_{CCIO} (V)			V_{IL} (V)		V_{IH} (V)		V_{OL} (V)	V_{OH} (V)	I_{OL} (mA)	I_{OH} (mA)
	Min	Typ	Max	Min	Max	Min	Max	Max	Min		
3.3 V LVTTL	3.135	3.3	3.465	–0.3	0.8	1.7	3.6	0.45	2.4	4	–4
3.3 V LVCMOS	3.135	3.3	3.465	–0.3	0.8	1.7	3.6	0.2	V_{CCIO} – 0.2	2	–2
3.0 V LVTTL	2.85	3	3.15	–0.3	0.8	1.7	V_{CCIO} + 0.3	0.45	2.4	4	–4
3.0 V LVCMOS	2.85	3	3.15	–0.3	0.8	1.7	V_{CCIO} + 0.3	0.2	V_{CCIO} – 0.2	0.1	–0.1
2.5 V LVTTL and LVCMOS	2.375	2.5	2.625	–0.3	0.7	1.7	V_{CCIO} + 0.3	0.4	2	1	–1
1.8 V LVTTL and LVCMOS	1.71	1.8	1.89	–0.3	0.35 × V_{CCIO}	0.65 × V_{CCIO}	2.25	0.45	V_{CCIO} – 0.45	2	–2
1.5 V LVCMOS	1.425	1.5	1.575	–0.3	0.35 × V_{CCIO}	0.65 × V_{CCIO}	V_{CCIO} + 0.3	0.25 × V_{CCIO}	0.75 × V_{CCIO}	2	–2
1.2 V LVCMOS	1.14	1.2	1.26	–0.3	0.35 × V_{CCIO}	0.65 × V_{CCIO}	V_{CCIO} + 0.3	0.25 × V_{CCIO}	0.75 × V_{CCIO}	2	–2
3.3 V Schmitt Trigger	3.135	3.3	3.465	–0.3	0.8	1.7	V_{CCIO} + 0.3	—	—	—	—
2.5 V Schmitt Trigger	2.375	2.5	2.625	–0.3	0.7	1.7	V_{CCIO} + 0.3	—	—	—	—
1.8 V Schmitt Trigger	1.71	1.8	1.89	–0.3	0.35 × V_{CCIO}	0.65 × V_{CCIO}	V_{CCIO} + 0.3	—	—	—	—
1.5 V Schmitt Trigger	1.425	1.5	1.575	–0.3	0.35 × V_{CCIO}	0.65 × V_{CCIO}	V_{CCIO} + 0.3	—	—	—	—
3.0 V PCI	2.85	3	3.15	—	0.3 × V_{CCIO}	0.5 × V_{CCIO}	V_{CCIO} + 0.3	0.1 × V_{CCIO}	0.9 × V_{CCIO}	1.5	–0.5

Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications

Table 21. Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications for Intel MAX 10 Devices

I/O Standard	V_{CCIO} (V)			V_{REF} (V)			V_{TT} (V) (14)		
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max
SSTL-2 Class I, II	2.375	2.5	2.625	1.19	1.25	1.31	V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04
SSTL-18 Class I, II	1.7	1.8	1.9	0.833	0.9	0.969	V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04
SSTL-15 Class I, II	1.425	1.5	1.575	0.49 × V_{CCIO}	0.5 × V_{CCIO}	0.51 × V_{CCIO}	0.49 × V_{CCIO}	0.5 × V_{CCIO}	0.51 × V_{CCIO}
SSTL-135 Class I, II	1.283	1.35	1.45	0.49 × V_{CCIO}	0.5 × V_{CCIO}	0.51 × V_{CCIO}	0.49 × V_{CCIO}	0.5 × V_{CCIO}	0.51 × V_{CCIO}
HSTL-18 Class I, II	1.71	1.8	1.89	0.85	0.9	0.95	0.85	0.9	0.95
HSTL-15 Class I, II	1.425	1.5	1.575	0.71	0.75	0.79	0.71	0.75	0.79
HSTL-12 Class I, II	1.14	1.2	1.26	0.48 × V_{CCIO} (15)	0.5 × V_{CCIO} (15)	0.52 × V_{CCIO} (15)	—	0.5 × V_{CCIO}	—
				0.47 × V_{CCIO} (16)	0.5 × V_{CCIO} (16)	0.53 × V_{CCIO} (16)			
HSUL-12	1.14	1.2	1.3	0.49 × V_{CCIO}	0.5 × V_{CCIO}	0.51 × V_{CCIO}	—	—	—

(14) V_{TT} of transmitting device must track V_{REF} of the receiving device.

(15) Value shown refers to DC input reference voltage, $V_{REF(DC)}$.

(16) Value shown refers to AC input reference voltage, $V_{REF(AC)}$.

Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications

Table 22. Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications for Intel MAX 10 Devices

To meet the I_{OL} and I_{OH} specifications, you must set the current strength settings accordingly. For example, to meet the SSTL-15 Class I specification (8 mA), you should set the current strength settings to 8 mA. Setting at lower current strength may not meet the I_{OL} and I_{OH} specifications in the datasheet.

I/O Standard	$V_{IL(DC)}$ (V)		$V_{IH(DC)}$ (V)		$V_{IL(AC)}$ (V)		$V_{IH(AC)}$ (V)		V_{OL} (V)	V_{OH} (V)	I_{OL} (mA)	I_{OH} (mA)
	Min	Max	Min	Max	Min	Max	Min	Max	Max	Min		
SSTL-2 Class I	—	V_{REF} – 0.18	V_{REF} + 0.18	—	—	V_{REF} – 0.31	V_{REF} + 0.31	—	V_{TT} – 0.57	V_{TT} + 0.57	8.1	–8.1
SSTL-2 Class II	—	V_{REF} – 0.18	V_{REF} + 0.18	—	—	V_{REF} – 0.31	V_{REF} + 0.31	—	V_{TT} – 0.76	V_{TT} + 0.76	16.4	–16.4
SSTL-18 Class I	—	V_{REF} – 0.125	V_{REF} + 0.125	—	—	V_{REF} – 0.25	V_{REF} + 0.25	—	V_{TT} – 0.475	V_{TT} + 0.475	6.7	–6.7
SSTL-18 Class II	—	V_{REF} – 0.125	V_{REF} + 0.125	—	—	V_{REF} – 0.25	V_{REF} + 0.25	—	0.28	V_{CCIO} – 0.28	13.4	–13.4
SSTL-15 Class I	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.175	V_{REF} + 0.175	—	0.2 × V_{CCIO}	0.8 × V_{CCIO}	8	–8
SSTL-15 Class II	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.175	V_{REF} + 0.175	—	0.2 × V_{CCIO}	0.8 × V_{CCIO}	16	–16
SSTL-135	—	V_{REF} – 0.09	V_{REF} + 0.09	—	—	V_{REF} – 0.16	V_{REF} + 0.16	—	0.2 × V_{CCIO}	0.8 × V_{CCIO}	—	—
HSTL-18 Class I	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	8	–8
HSTL-18 Class II	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	16	–16
HSTL-15 Class I	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	8	–8
HSTL-15 Class II	—	V_{REF} – 0.1	V_{REF} + 0.1	—	—	V_{REF} – 0.2	V_{REF} + 0.2	—	0.4	V_{CCIO} – 0.4	16	–16

continued...

I/O Standard	$V_{IL(DC)}$ (V)		$V_{IH(DC)}$ (V)		$V_{IL(AC)}$ (V)		$V_{IH(AC)}$ (V)		V_{OL} (V)	V_{OH} (V)	I_{OL} (mA)	I_{OH} (mA)
	Min	Max	Min	Max	Min	Max	Min	Max	Max	Min		
HSTL-12 Class I	–0.15	V_{REF} – 0.08	V_{REF} + 0.08	V_{CCIO} + 0.15	–0.24	V_{REF} – 0.15	V_{REF} + 0.15	V_{CCIO} + 0.24	0.25 × V_{CCIO}	0.75 × V_{CCIO}	8	–8
HSTL-12 Class II	–0.15	V_{REF} – 0.08	V_{REF} + 0.08	V_{CCIO} + 0.15	–0.24	V_{REF} – 0.15	V_{REF} + 0.15	V_{CCIO} + 0.24	0.25 × V_{CCIO}	0.75 × V_{CCIO}	14	–14
HSUL-12	—	V_{REF} – 0.13	V_{REF} + 0.13	—	—	V_{REF} – 0.22	V_{REF} + 0.22	—	0.1 × V_{CCIO}	0.9 × V_{CCIO}	—	—

Differential SSTL I/O Standards Specifications

Differential SSTL requires a V_{REF} input.

Table 23. Differential SSTL I/O Standards Specifications for Intel MAX 10 Devices

I/O Standard	V_{CCIO} (V)			$V_{Swing(DC)}$ (V)		$V_{X(AC)}$ (V)			$V_{Swing(AC)}$ (V)	
	Min	Typ	Max	Min	Max[17]	Min	Typ	Max	Min	Max
SSTL-2 Class I, II	2.375	2.5	2.625	0.36	V_{CCIO}	$V_{CCIO}/2$ – 0.2	—	V_{CCIO}/ 2+ 0.2	0.7	V_{CCIO}
SSTL-18 Class I, II	1.7	1.8	1.9	0.25	V_{CCIO}	$V_{CCIO}/2$ – 0.175	—	V_{CCIO}/ 2+ 0.175	0.5	V_{CCIO}
SSTL-15 Class I, II	1.425	1.5	1.575	0.2	—	$V_{CCIO}/2$ – 0.15	—	$V_{CCIO}/2$ + 0.15	$2(V_{IH(AC)} – V_{REF})$	$2(V_{IL(AC)} – V_{REF})$
SSTL-135	1.283	1.35	1.45	0.18	—	V_{REF} – 0.135	0.5 × V_{CCIO}	V_{REF} + 0.135	$2(V_{IH(AC)} – V_{REF})$	$2(V_{IL(AC)} – V_{REF})$

Differential HSTL and HSUL I/O Standards Specifications

Differential HSTL requires a V_{REF} input.

(17) The maximum value for $V_{SWING(DC)}$ is not defined. However, each single-ended signal needs to be within the respective single-ended limits ($V_{IH(DC)}$ and $V_{IL(DC)}$).

Table 24. Differential HSTL and HSUL I/O Standards Specifications for Intel MAX 10 Devices

I/O Standard	V_{CCIO} (V)			$V_{DIF(DC)}$ (V)		$V_{X(AC)}$ (V)			$V_{CM(DC)}$ (V)			$V_{DIF(AC)}$ (V)
	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max	Min
HSTL-18 Class I, II	1.71	1.8	1.89	0.2	—	0.85	—	0.95	0.85	—	0.95	0.4
HSTL-15 Class I, II	1.425	1.5	1.575	0.2	—	0.71	—	0.79	0.71	—	0.79	0.4
HSTL-12 Class I, II	1.14	1.2	1.26	0.16	V_{CCIO}	0.48 × V_{CCIO}	0.5 × V_{CCIO}	0.52 × V_{CCIO}	0.48 × V_{CCIO}	0.5 × V_{CCIO}	0.52 × V_{CCIO}	0.3
HSUL-12	1.14	1.2	1.3	0.26	—	0.5 × V_{CCIO} – 0.12	0.5 × V_{CCIO}	0.5 × V_{CCIO} + 0.12	0.4 × V_{CCIO}	0.5 × V_{CCIO}	0.6 × V_{CCIO}	0.44

Differential I/O Standards Specifications

Table 25. Differential I/O Standards Specifications for Intel MAX 10 Devices

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{ICM} (V) (18)			V_{OD} (mV) (19)(20)			V_{OS} (V) (19)		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
LVPECL (21)	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	—	—	—	—	—	—
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						
						1.05	D_{MAX} > 700 Mbps	1.55						
LVDS	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	247	—	600	1.125	1.25	1.375
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						

continued...

(18) V_{IN} range: 0 V ≤ V_{IN} ≤ 1.85 V.

(19) R_L range: 90 ≤ R_L ≤ 110 Ω.

(20) Low V_{OD} setting is only supported for RSDS standard.

(21) LVPECL input standard is only supported at clock input. Output standard is not supported.

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{ICM} (V) (18)			V_{OD} (mV) (19)(20)			V_{OS} (V) (19)		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
						1.05	D_{MAX} > 700 Mbps	1.55						
BLVDS (22)	2.375	2.5	2.625	100	—	—	—	—	—	—	—	—	—	—
mini-LVDS (23)	2.375	2.5	2.625	—	—	—	—	—	300	—	600	1	1.2	1.4
RSDS (23)	2.375	2.5	2.625	—	—	—	—	—	100	200	600	0.5	1.2	1.5
PPDS (Row I/Os) (23)	2.375	2.5	2.625	—	—	—	—	—	100	200	600	0.5	1.2	1.4
TMDS(24)	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	—	—	—	—	—	—
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						
						1.05	D_{MAX} > 700 Mbps	1.55						
Sub-LVDS (25)	1.71	1.8	1.89	100	—	0.55	—	1.25	(26)			0.8	0.9	1
SLVS	2.375	2.5	2.625	100	—	0.05	—	1.1	(26)			(27)		

continued...

(18) V_{IN} range: 0 V ≤ V_{IN} ≤ 1.85 V.
(19) R_L range: 90 ≤ R_L ≤ 110 Ω.
(20) Low V_{OD} setting is only supported for RSDS standard.

I/O Standard	V_{CCIO} (V)			V_{ID} (mV)		V_{ICM} (V) (18)			V_{OD} (mV) (19)(20)			V_{OS} (V) (19)		
	Min	Typ	Max	Min	Max	Min	Condition	Max	Min	Typ	Max	Min	Typ	Max
HiSpi	2.375	2.5	2.625	100	—	0.05	D_{MAX} ≤ 500 Mbps	1.8	—	—	—	—	—	—
						0.55	500 Mbps ≤ D_{MAX} ≤ 700 Mbps	1.8						
						1.05	D_{MAX} > 700 Mbps	1.55						

Related Information

Intel MAX 10 LVDS SERDES I/O Standards Support, Intel MAX 10 High-Speed LVDS I/O User Guide
Provides the list of I/O standards supported in single supply and dual supply devices.

Switching Characteristics

This section provides the performance characteristics of Intel MAX 10 core and periphery blocks.

(18) V_{IN} range: 0 V ≤ V_{IN} ≤ 1.85 V.
(19) R_L range: 90 ≤ R_L ≤ 110 Ω.
(20) Low V_{OD} setting is only supported for RSDS standard.

(22) No fixed V_{IN} , V_{OD} , and V_{OS} specifications for Bus LVDS (BLVDS). They are dependent on the system topology.

(23) Mini-LVDS, RSDS, and Point-to-Point Differential Signaling (PPDS) standards are only supported at the output pins for Intel MAX 10 devices.

(24) Supported with requirement of an external level shift

(25) Sub-LVDS input buffer is using 2.5 V differential buffer.

(26) Differential output depends on the values of the external termination resistors.

(27) Differential output offset voltage depends on the values of the external termination resistors.